

Fast Recovery Diodes (Hockey PUK Version), 600 A



PRIMARY CHARACTERISTICS				
I _{F(AV)} 600 A				
Package	B-43			
Circuit configuration	Single			

FEATURES

- High power fast recovery diode series
- 1.0 µs to 2.0 µs recovery time
- High voltage ratings up to 2200 V
- High current capability
- · Optimized turn-on and turn-off characteristics
- Low forward recovery
- · Fast and soft reverse recovery
- Press PUK encapsulation
- Case style conform to JEDEC® B-43
- Maximum junction temperature 125 °C
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- Snubber diode for GTO
- · High voltage freewheeling diode
- Fast recovery rectifier applications

MAJOR RATINGS AND CHARACTERISTICS						
	TEST CONDITIONS					
PARAMETER	TEST CONDITIONS	S10	S15	S20	UNITS	
1		600	600	600	Α	
I _{F(AV)}	T _{hs}	55	55	55	°C	
1		942	942	942	Α	
I _F (RMS)	T _{hs}	25	25	25	°C	
1	50 Hz	8320	8320	8320	- A	
I _{FSM}	60 Hz	8715	8715	8715		
l ² t	50 Hz	346	346	346	kA ² s	
	60 Hz	316	316	316		
V _{RRM}	Range	400 to 1000	1200 to 1600	2000 to 2200	V	
		1.0	1.5	2.0	μs	
t _{rr}	T _J	25	25	25	°C	
TJ		-40 to +125	-40 to +125	-40 to +125		

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I _{RRM} MAXIMUM AT T _J = 125 °C mA			
	04	400	500				
VS-SD603CS10C	08	800	900				
	10	1000	1100				
	12	1200	1300	45			
VS-SD603CS15C	14	1400	1500	45			
	16	1600	1700				
VC CDC00C C00C	20	2000	2100				
VS-SD603CS20C	22	2200	2300				

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FORWARD CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average forward current	I _{F(AV)}	180° conduction, half sine wave		600 (300)	Α	
at heatsink temperature	. (*)	Double sid	e (single side) o	coolea	55 (75)	°C
Maximum RMS current	I _{F(RMS)}	25 °C heat	sink temperatu	re double side cooled	942	
		t = 10 ms	No voltage		8320	
Maximum peak, one-cycle	leo,	t = 8.3 ms	reapplied		8715	Α
non-repetitive forward current	I _{FSM}	t = 10 ms	100 % V _{RRM}		7000	
		t = 8.3 ms	reapplied	Sinusoidal half wave, initial $T_{.1} = T_{.1}$	7330	
	l ² t	t = 10 ms	No voltage	maximum	346	kA ² s
Maximum I ² t for fusing		t = 8.3 ms	reapplied		316	
I Waxii idiii i-t ioi iusiiig		t = 10 ms	100 % V _{RRM}		245	
		t = 8.3 ms	reapplied		224	
Maximum I ² √t for fusing	I²√t	t = 0.1 to 10 ms, no voltage reapplied			3460	kA²√s
Low level value of threshold voltage	V _{F(TO)1}	(16.7 % x π x I _{F(AV)} < I < π x I _{F(AV)}), T _J = T _J maximum			1.36	V
High level value of threshold voltage	V _{F(TO)2}	$(I > \pi \times I_{F(AV)}), T_J = T_J \text{ maximum}$			1.81	V
Low level of forward slope resistance	r _{f1}	(16.7 % x π x I _{F(AV)} < I < π x I _{F(AV)}), T _J = T _J maximum			0.87	mW
High level of forward slope resistance	r _{f2}	$(I > \pi \times I_{F(AV)}), T_J = T_J \text{ maximum}$			0.67	11100
Maximum forward voltage drop	V_{FM}	$I_{pk} = 1885$	A, $T_J = 25 ^{\circ}\text{C}$; t_p	= 10 ms sinusoidal wave	2.97	V

RECO	RECOVERY CHARACTERISTICS							
	MAXIMUM VALUE AT T _J = 25 °C	TEST CONDITIONS		TYPICAL VALUES AT T _J = 125 °C				
CODE	t _{rr} AT 25 % I _{RRM} (µs)	I _{pk} SQUARE PULSE (A)	dl/dt (A/µs)	V _r (V)	t _{rr} AT 25 % I _{RRM} (µs)	Q _{rr} (μC)	I _{rr} (A)	I _{FM} t _{rr}
S10	1.0				2.0	45	34	dir/ dt Q _{rr}
S15	1.5	1000	25	-30	3.2	87	51	I I I I I I I I I I I I I I I I I I I
S20	2.0				3.5	97	55	, ,,

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	TJ		-40 to 125	°C	
Maximum storage temperature range	T _{Stg}		-40 to 150	C	
Maximum thermal resistance,	R _{thJ-hs}	DC operation single side cooled	0.076	K/W	
junction to heatsink		DC operation double side cooled	0.038		
Mounting force, ± 10 %			9800 (1000)	N (kg)	
Approximate weight			83	g	
Case style		See dimensions - link at the end of datasheet	B-4	3	

△R _{thJ-hs} CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL C	ONDUCTION	RECTANGULA	R CONDUCTION	TEST CONDITIONS	UNITS	
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS		
180°	0.006	0.007	0.005	0.005			
120°	0.008	0.008	0.008	0.008			
90°	0.010	0.010	0.011	0.011	$T_J = T_J$ maximum	K/W	
60°	0.015	0.015	0.016	0.015			
30°	0.026	0.025	0.026	0.025			

Note

[•] The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

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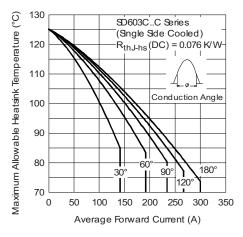


Fig. 1 - Current Ratings Characteristics

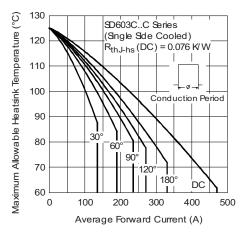


Fig. 2 - Current Ratings Characteristics

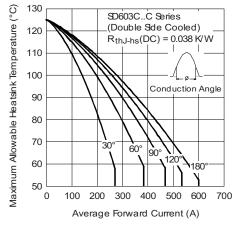


Fig. 3 - Current Ratings Characteristics

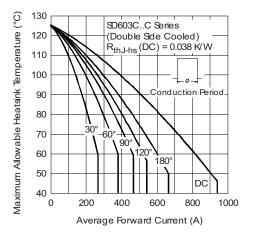


Fig. 4 - Current Ratings Characteristics

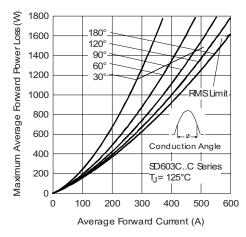


Fig. 5 - Forward Power Loss Characteristics

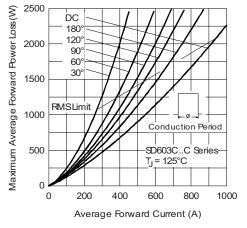


Fig. 6 - Forward Power Loss Characteristics

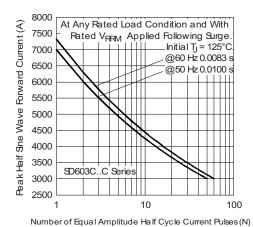


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

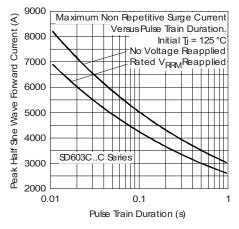


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

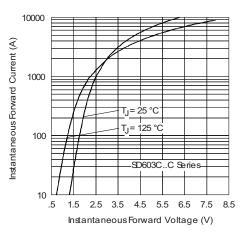


Fig. 9 - Forward Voltage Drop Characteristics

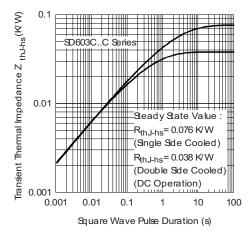


Fig. 10 - Thermal Impedance $Z_{thJ\text{-}hs}$ Characteristics

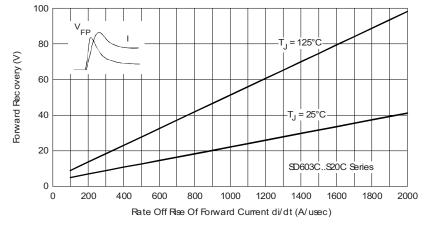
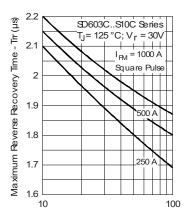


Fig. 11 - Typical Forward Recovery Characteristics



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Rate Of Fall Of Forward Current - di/dt (A/µs)

Fig. 12 - Recovery Time Characteristics

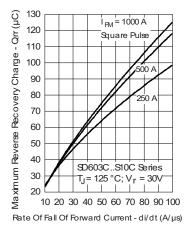


Fig. 13 - Recovery Charge Characteristics

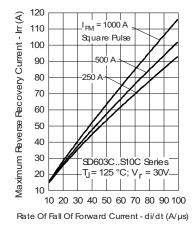
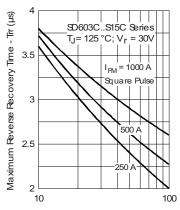


Fig. 14 - Recovery Current Characteristics



Rate Of Fall Of Forward Current - di/dt (A/µs)

Fig. 15 - Recovery Time Characteristics

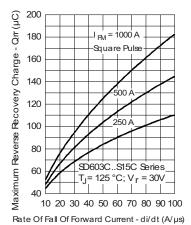


Fig. 16 - Recovery Charge Characteristics

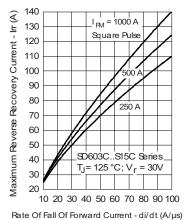


Fig. 17 - Recovery Current Characteristics

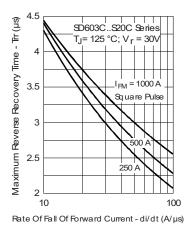


Fig. 18 - Recovery Time Characteristics

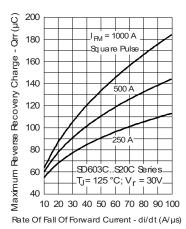


Fig. 19 - Recovery Charge Characteristics

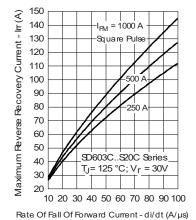
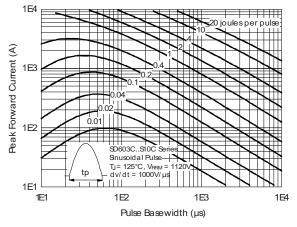


Fig. 20 - Recovery Current Characteristics



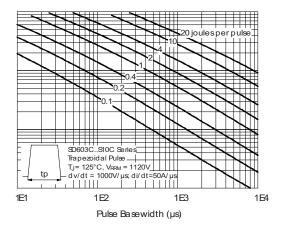
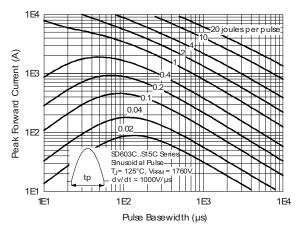


Fig. 21 - Maximum Total Energy Loss Per Pulse Characteristics





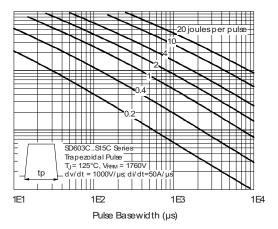
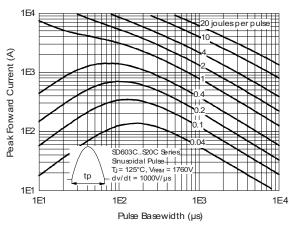


Fig. 22 - Maximum Total Energy Loss Per Pulse Characteristics



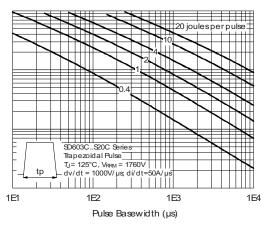
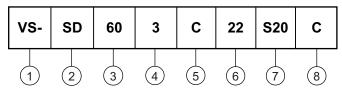


Fig. 23 - Maximum Total Energy Loss Per Pulse Characteristics

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

|**2**| - Diode

Essential part number

4 - 3 = fast recovery

5 - C = ceramic PUK

6 - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)

t_{rr} code (see Recovery Characteristics table)

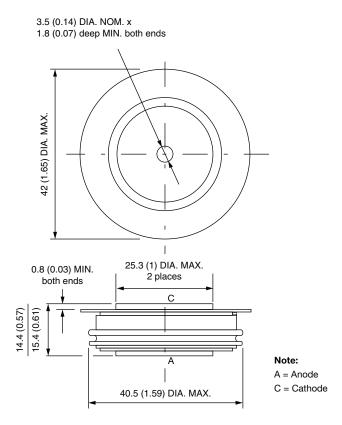
8 - C = PUK case B-43

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95249			



B-43

DIMENSIONS in millimeters (inches)



Quote between upper and lower pole pieces has to be considered after application of mounting force (see Thermal and Mechanical Specifications)



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